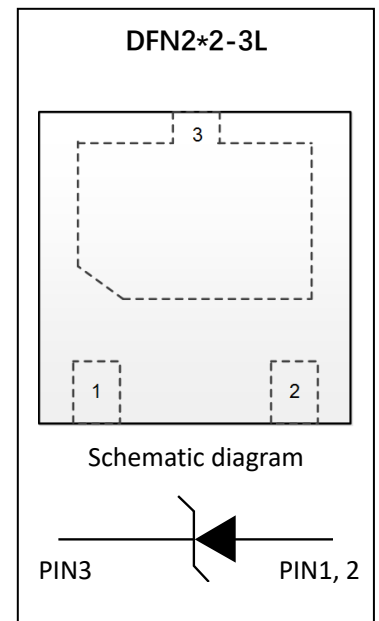


Product Summary

The GESDS12VP1P is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line.

Feature

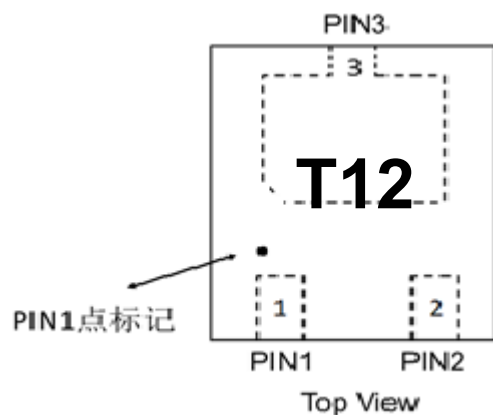
- Low reverse stand-off voltage: 12V
- Low reverse clamping voltage
- Low leakage current
- Fast response time
- JESD22-A114-B ESD Rating of class 3B per human body model
- IEC 61000-4-2 Level 4 ESD protection



Application

- Computers and peripherals
- Portable electronics
- Power lines
- Audio and video equipment
- Cellular handsets and accessories
- Other electronic equipment communication systems

Marking:



Front Side
T12=Device Code

Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
IEC 61000-4-2 ESD Voltage Air Model	$V_{\text{ESD}}^{1)}$	± 30	kV
IEC 61000-4-2 ESD Voltage Contact Model		± 30	
JESD22-A114-B ESD Voltage Per Human Body Model		± 16	
ESD Voltage Machine Model		± 0.4	
Peak Pulse Power	$P_{\text{PP}}^{2)}$	4500	W
Peak Pulse Current	$I_{\text{PP}}^{2)}$	180	A
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	$^{\circ}\text{C}$
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~ +150	$^{\circ}\text{C}$

- 1) Device stressed with ten non-repetitive ESD pulses.
- 2) Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5.

ESD standards compliance

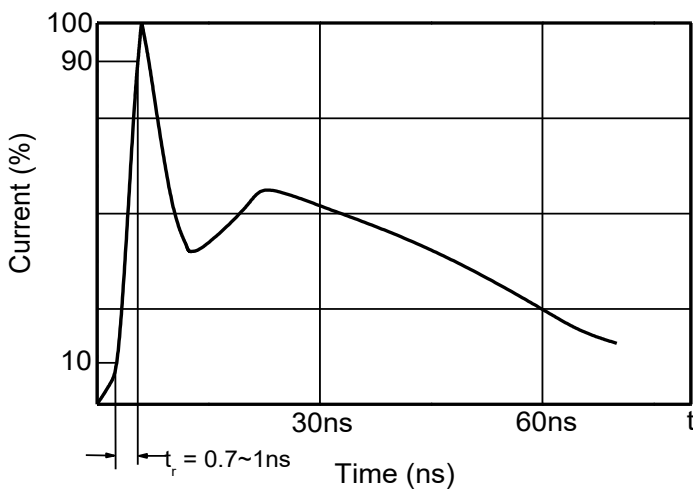
IEC61000-4-2 Standard

Contact Discharge		Air Discharge	
Level	Test Voltage kV	Level	Test Voltage kV
1	2	1	2
2	4	2	4
3	6	3	8
4	8	4	15

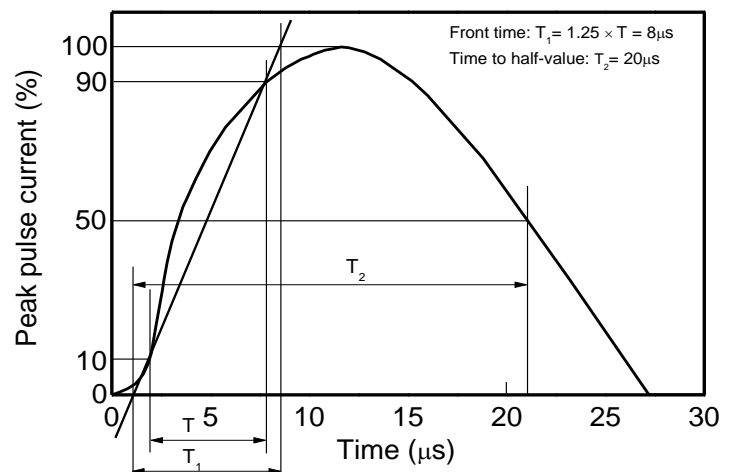
JESD22-A114-B Standard

ESD Class	Human Body Discharge V
0	0~249
1A	250~499
1B	500~999
1C	1000~1999
2	2000~3999
3A	4000~7999
3B	8000~15999

Contact discharge current waveform per IEC61000-4-2

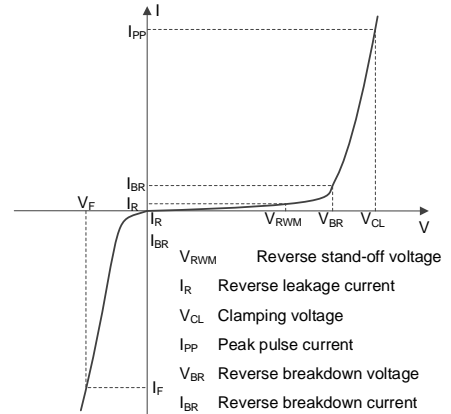


8/20 μs waveform per IEC61000-4-5



Electrical Parameter

Symbol	Parameter
V _C	Clamping Voltage @ I _{PP}
I _{PP}	Peak Pulse Current
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
I _R	Reverse Leakage Current @ V _{RWM}
V _{RWM}	Reverse Standoff Voltage



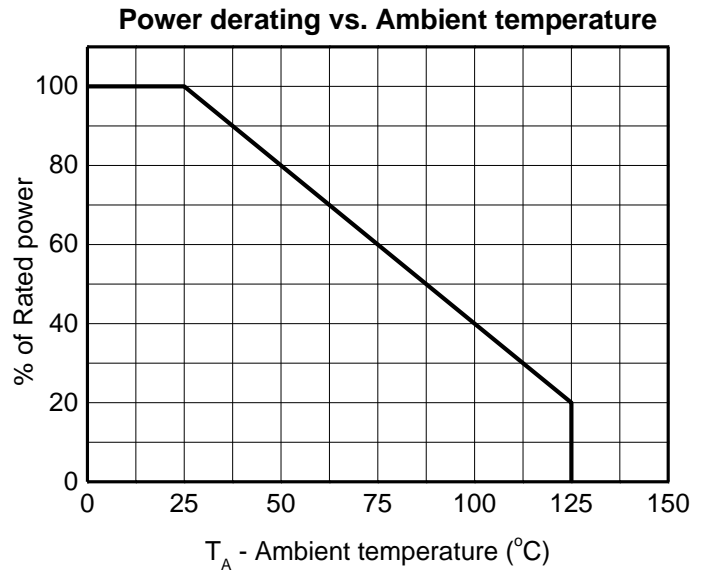
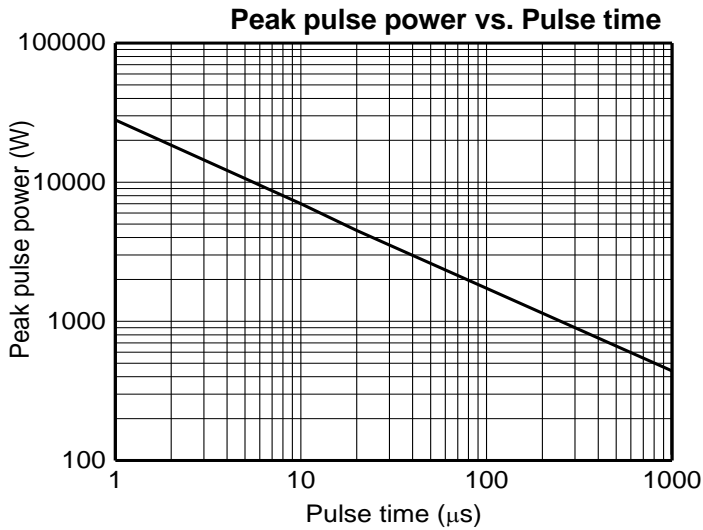
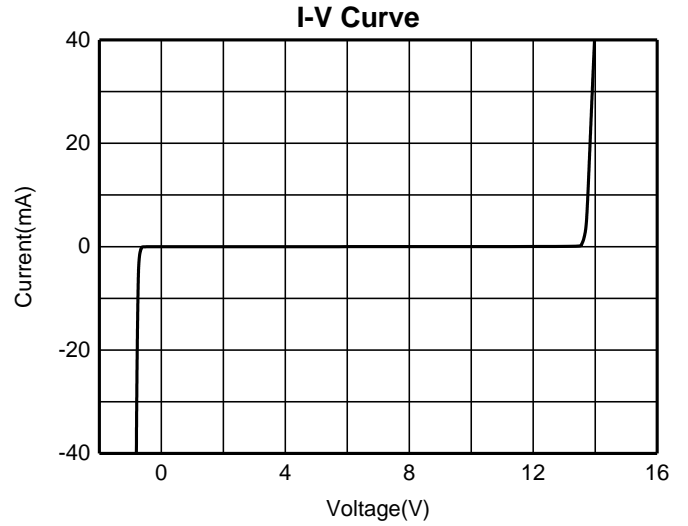
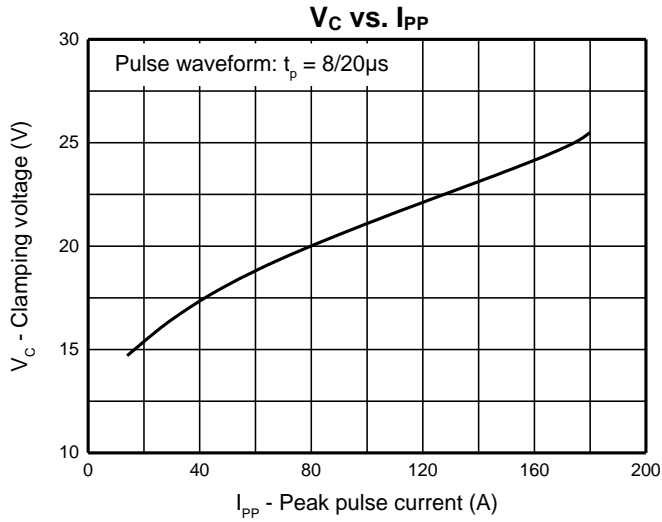
V-I characteristics for a Uni-directional TVS

Electrical Characteristics (Ta=25°C unless otherwise specified)

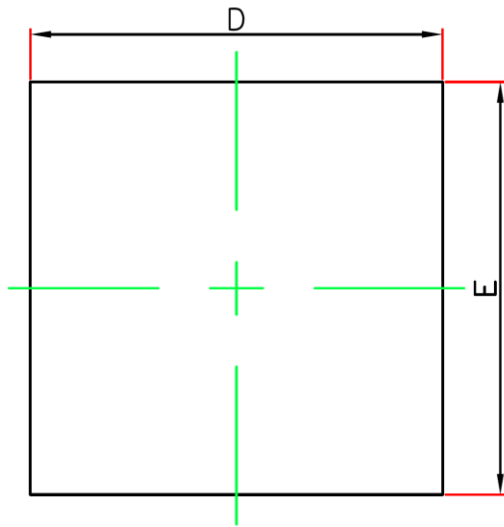
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse stand-off voltage	V _{RWM} ¹⁾				12	V
Reverse leakage current	I _R	V _{RWM} =12V			1	uA
Breakdown voltage	V _{BR}	I _T =1mA	13.5			V
Clamping voltage	V _C ²⁾	I _{PP} =50A		18.8		V
		I _{PP} =170A		24.5	28.5	V
Junction capacitance	C _J	V _R =0V, f=1MHz		1.4		nF

- 1) Other voltages available upon request.
- 2) Non-repetitive current pulse 8/20μs exponential decay waveform according to IEC61000-4-5

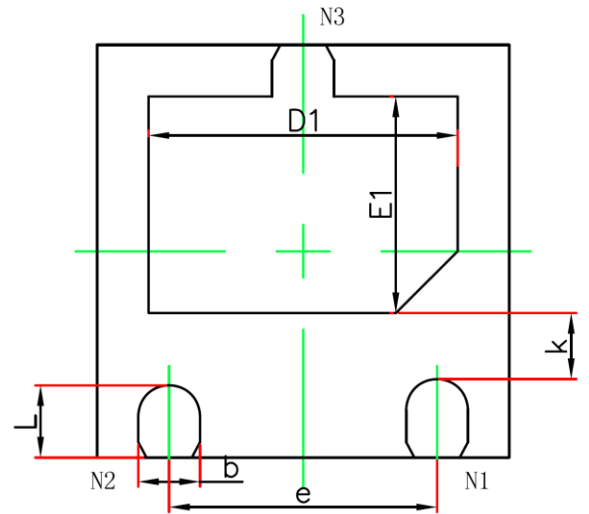
Typical Characteristics



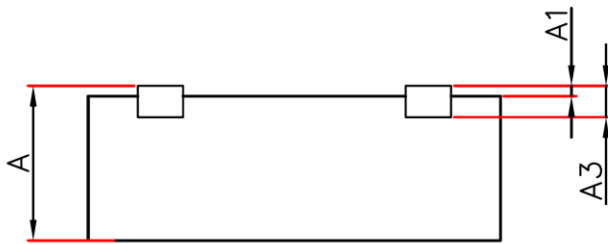
DFN2*2-3L Package Outline Dimensions



TOP VIEW
[顶视图]



BOTTOM VIEW
[背视图]



SIDE VIEW
[侧视图]

Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.550	0.650
A1	0.000	0.050
A3	0.152REF.	
D	1.924	2.076
E	1.924	2.076
D1	1.400	1.600
E1	0.950	1.150
K	0.220Min.	
b	0.250	0.350
e	1.30(BSC)	
L	0.330	0.430